

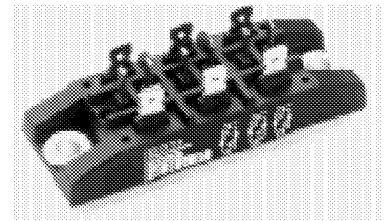
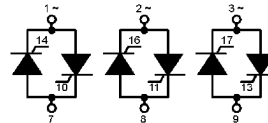
Three Phase AC Controller Modules

$$I_{RMS} = 3 \times 39 \text{ A}$$

$$V_{RRM} = 800 - 1600 \text{ V}$$

Preliminary data

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
800	800	VWO 36-08io7
1200	1200	VWO 36-12io7
1400	1400	VWO 36-14io7
1600	1600	VWO 36-16io7



Symbol	Test Conditions		Maximum Ratings	
I _{RMS}	T _K = 85°C, 50 - 400 Hz (per phase)		39	A
I _{TRMS}	T _{VJ} = T _{VJM}		28	A
I _{TAVM}	T _K = 85°C; (180° sine)		18	A
I _{TSM}	T _{VJ} = 45°C;	t = 10 ms (50 Hz), sine	320	A
	V _R = 0	t = 8.3 ms (60 Hz), sine	350	A
	T _{VJ} = T _{VJM}	t = 10 ms (50 Hz), sine	280	A
	V _R = 0	t = 8.3 ms (60 Hz), sine	310	A
I ² t	T _{VJ} = 45°C	t = 10 ms (50 Hz), sine	500	A ² s
	V _R = 0	t = 8.3 ms (60 Hz), sine	520	A ² s
	T _{VJ} = T _{VJM}	t = 10 ms (50 Hz), sine	390	A ² s
	V _R = 0	t = 8.3 ms (60 Hz), sine	400	A ² s
(di/dt) _{cr}	T _{VJ} = T _{VJM} f =50 Hz, t _p =200 μs V _D = 2/3 V _{DRM} I _G = 0.3 A di _G /dt = 0.3 A/μs	repetitive, I _T = 20 A	150	A/μs
		non repetitive, I _T = I _{TAVM}	500	A/μs
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/μs
P _{GM}	T _{VJ} = T _{VJM}	t _p = 30 μs	10	W
	I _T = I _{TAVM}	t _p = 300 μs	5	W
P _{GAVM}			0.5	W
V _{RGM}			10	V
T _{VJ}			-40...+125	°C
T _{VJM}			125	°C
T _{stg}			-40...+125	°C
V _{ISOL}	50/60 Hz, RMS	t = 1 min	2500	V~
	I _{ISOL} ≤ 1 mA	t = 1 s	3000	V~
M _d	Mounting torque (M5)		5 ± 15 %	Nm
	(10-32 UNF)		44 ± 15 %	lb.in.
Weight	typ.		110	g

Features

- ☐ Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- ☐ Package with metal base plate
- ☐ Isolation voltage 3000 V~
- ☐ Planar passivated chips
- ☐ UL applied
- ☐ 1/4" fast-on power terminals

Applications

- ☐ Switching and control of three phase AC circuits
- ☐ Softstart AC motor controller
- ☐ Solid state switches
- ☐ Light and temperature control

Advantages

- ☐ Easy to mount with two screws
- ☐ Space and weight savings
- ☐ Improved temperature and power cycling capability
- ☐ High power density
- ☐ Light weight and compact

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
IXYS reserves the right to change limits, test conditions and dimensions

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Symbol	Test Conditions	Characteristic Values	
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	$\leq$	5 mA
V_T	$I_T = 45 \text{ A}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.45 V
V_{T0}	For power-loss calculations only ($T_{VJ} = 125^\circ\text{C}$)	0.85	V
r_T		13	m Ω
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.0 V
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	1.2 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	65 mA
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	80 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	$\leq$	0.2 V
I_{GD}		$\leq$	5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}; di_e/dt = 0.3 \text{ A}/\mu\text{s}$	$\leq$	150 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	$\leq$	100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}; di_e/dt = 0.3 \text{ A}/\mu\text{s}$	$\leq$	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}; t_p = 200 \mu\text{s}; di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150 μs
R_{thJC}	per thyristor; sine 180°el	1.3	K/W
	per module	0.216	K/W
R_{thJK}	per thyristor; sine 180°el	1.5	K/W
	per module	0.25	K/W
d_s	Creeping distance on surface	16.1	mm
d_A	Creepage distance in air	6.0	mm
a	Max. allowable acceleration	50	m/s ²

Dimensions in mm (1 mm = 0.0394")

